



QUESTION PAPER

Name of the Examination: WINTER 2022-2023 – FAT

Course Code: PHY 1008

Course Title: Modern Physics

Set number: 01

Date of Exam: 16/06/2023 (Ans) (16)

Duration: 120 minutes

Total Marks: 60

Instructions:

1. Assume data wherever necessary.
2. Any assumptions made should be clearly stated.
3. Use the following values, $h = 6.63 \times 10^{-34}$ J s, $e = 1.6 \times 10^{-19}$ C, $m_e = 9.11 \times 10^{-31}$ kg, $m_n = 1.67 \times 10^{-27}$ kg, $m_p = 1.67 \times 10^{-27}$ kg, $c = 3 \times 10^8$ m/s, $1 \text{ eV} = 1.6 \times 10^{-19}$ J, $k_B = 1.38 \times 10^{-23}$ J K⁻¹ = 8.617×10^{-5} eV K⁻¹, $\mu_0 = 4\pi \times 10^{-7}$ H/m, Avogadro Number (N_A) = 6.023×10^{23} /mol, Bohr Magnetron (μ_B or β) = 9.27×10^{-24} A m², wherever required.

Q1. A particle is in the ground state of an infinite square well potential, which extends from $x = 0$ to $x = L$. Determine the probability that the particle is confined within a length of $x = 0$ and $x = L/4$.

(10 marks)

Q2. A certain intrinsic germanium rod is 1 cm long, 1 mm wide and 1 mm thick. The rod carries current along its length. The intrinsic carrier density at 300 K is $2.5 \times 10^{19} \text{ m}^{-3}$ and the mobilities of electron and hole are 0.39 and $0.19 \text{ m}^2 \text{ V}^{-1} \text{ s}^{-1}$, respectively.

Find the resistance of the rod at 300 K.

(10 marks)

Q3. Consider silicon at $T = 300$ K, having a band gap energy of 1.12 eV, with $N_c = 2.8 \times 10^{19} \text{ cm}^{-3}$ and $N_v = 1.04 \times 10^{19} \text{ cm}^{-3}$. If the Fermi energy is 0.25 eV below the conduction band, find the thermal equilibrium concentration of electrons and holes. Take $k = 8.6 \times 10^{-5} \text{ eV/K}$ as the Boltzmann constant.

(10 marks)

Q4. The energy of a photon in Sodium light of wavelength $\lambda = 589 \text{ nm}$, equals the band-gap energy (E_g) of a semiconducting material.

- (a) Find the minimum energy required to create an electron-hole pair.
- (b) Find the value of E_g/kT , at $T = 300$ K, where T is the absolute temperature. From this value, could you say if it is easier to generate an electron-hole pair thermally, or by irradiation with Sodium light?

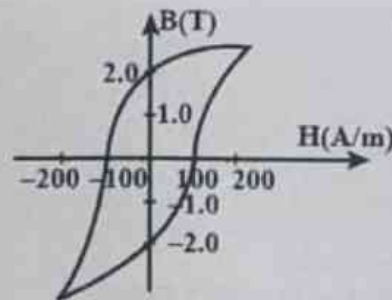
Here $k = 8.6 \times 10^{-5}$ eV/K is the Boltzmann constant.

(10 marks)

Q5. The magnetic flux density within a bar of some material is 0.63 Tesla at an external field of 5×10^5 A/m. Compute the magnetic permeability, and magnetic susceptibility for this material. Justify as to what type of magnetism is being displayed by the material.

(10 marks)

Q6. The B-H curve for a certain ferromagnetic material is as below:



From the curve identify the values of retentivity and coercivity.

Draw the M-H plots for a paramagnetic and diamagnetic material.

(10 marks)

QP MAPPING

Q. No.	Module Number	CO Mapped	PO Mapped	PEO Mapped	PSO Mapped	Marks
Q1	3	2	1,2,3,4,5,6,7	-	-	10
Q2	4	3,5	1,2,3,4,5,6,7	-	-	10
Q3	4	3,5	1,2,3,4,5,6,7	-	-	10
Q4	4	3,5	1,2,3,4,5,6,7	-	-	10
Q5	5	4,5	1,2,3,4,5,6,7	-	-	10
Q6	5	1,5	1,2,3,4,5,6,7	-	-	10



QUESTION PAPER

Name of the Examination: WINTER 2022-2023 – FAT

Course Code : PHY1008
Set number : 04
Duration : 120 Minutes

Course Title : Modern Physics
Date of Exam : 20/06/2023 (FN) (DI)
Total Marks : 60 Marks

Instructions:

1. Assume data wherever necessary.
2. Any assumptions made should be clearly stated.
3. Use the following values, $h = 6.63 \times 10^{-34}$ J s, $e = 1.6 \times 10^{-19}$ C, $m_e = 9.11 \times 10^{-31}$ kg, $m_n = 1.67 \times 10^{-27}$ kg, $m_p = 1.67 \times 10^{-27}$ kg, $c = 3 \times 10^8$ m/s, $1 \text{ eV} = 1.6 \times 10^{-19}$ J, $k_B = 1.38 \times 10^{-23}$ J K⁻¹ = 8.617×10^{-5} eV K⁻¹, $\mu_0 = 4\pi \times 10^{-7}$ H/m, Avogadro Number (N_A) = 6.023×10^{23} /mol, Bohr Magnetron (μ_B or β) = 9.27×10^{-24} A m², wherever required.

- Q1.** The normalized wave function of a particle trapped in a one-dimensional box of length L is given by $\psi = \sqrt{2/L} \sin(n\pi x/L)$. Compute the probability that the particle can be found between $0.45 L$ and $0.55 L$ in the first excited state. (10 Marks)
- Q2.** Calculate the intrinsic concentration in silicon at (a) $T = 200$ K and (b) $T = 450$ K. The values of effective density of states function in the conduction band and valence band for silicon at 300 K are $N_c = 2.8 \times 10^{19} \text{ cm}^{-3}$ and $N_v = 1.04 \times 10^{19} \text{ cm}^{-3}$, respectively. Both N_c and N_v , vary as $T^{3/2}$. Assume the band gap of silicon as 1.12 eV and does not vary over this temperature range. (10 Marks)
- Q3.** Determine the position of the intrinsic Fermi level at $T = 300$ K with respect to the center of the band gap for (a) GaAs and (b) Ge. The effective carrier masses (electron (m_e^*) and hole (m_h^*) in GaAs and Ge at 300 K are given as follows. For GaAs, $m_e^* = 0.067 m_0$ & $m_h^* = 0.48 m_0$ and for Ge, $m_e^* = 0.55 m_0$ and $m_h^* = 0.37 m_0$. (10 Marks)
- Q4.** (a) An n-type semiconductor is known to have an electron concentration of $1.0 \times 10^{18} \text{ m}^{-3}$. If the electron drift velocity is 60 m/s in an electric field of 300 V/m, calculate the conductivity of the material. (5 Marks)
- (b) A sample of intrinsic silicon at room temperature has a carrier concentration of $2.5 \times 10^{19} \text{ m}^{-3}$. It is doped with arsenic at a rate of one arsenic atom per million atoms of silicon. If the concentration of the silicon atoms is $5.0 \times 10^{28} \text{ m}^{-3}$. Determine the hole concentration. (5 Marks)

Q5. When a magnetic field (H) of 150 A/m is applied to some metal alloy, the magnetization in the alloy is 1.7×10^6 A/m. Determine the following (a) magnetic susceptibility (b) permeability (c) magnetic flux density within this material (d) identify the type of magnetism present in the metal alloy.

(10 Marks)

Q6. (a) An iron bar magnet having a coercivity of 4000 A/m is to be demagnetized. If the bar is inserted within a cylindrical wire coil (a solenoid) 25 cm long and having 150 turns, what electric current is required to generate the necessary magnetic field?

(5 Marks)

(b) The retentivity and coercive field of a ferromagnetic material are 1.25 T and 9000 A/m, respectively. The saturation magnetization is achieved when the magnetic field intensity is 15,000 A/m and the corresponding magnetic flux density is 1.5 T. From the given data, draw the complete hysteresis curve in the range $H = -15,000$ to $+15,000$ A/m. Correctly indicate the scale and label both coordinate axes.

(5 Marks)

QP MAPPING

Q. No.	Module Number	CO Mapped	PO Mapped	PEO Mapped	PSO Mapped	Marks
Q1	3	2	1, 2, 3, 4 & 5	1, 2, 3 & 4	1, 2 & 3	10
Q2	4	3	1, 2, 3, 4, 5, 6 & 7	1, 2, 3 & 4	1, 2 & 3	10
Q3	4	3	1, 2, 3, 4, 5, 6 & 7	1, 2, 3 & 4	1, 2 & 3	10
Q4	4	5	1, 2, 3, 4, 5, 6 & 7	1, 2, 3 & 4	1, 2 & 3	10
Q5	5	4	1, 2, 3, 4, 5, 6 & 7	1, 2, 3 & 4	1, 2 & 3	10
Q5	5	4	1, 2, 3, 4, 5, 6 & 7	1, 2, 3 & 4	1, 2 & 3	10

QUESTION PAPER

Name of the Examination: WIN SEM 2022-2023 - FAT

Course Code: PHY1008

Set number: 07

Duration: 120 Min

Course Title: Modern Physics

Date of Exam: 20/06/2023 (AM) (D2)

Total Marks: 60 Marks

Instructions:

1. Assume data wherever necessary.
2. Any assumptions made should be clearly stated.
3. Use the following values, $h = 6.63 \times 10^{-34}$ J s, $e = 1.6 \times 10^{-19}$ C, $m_e = 9.11 \times 10^{-31}$ kg, $m_n = 1.67 \times 10^{-27}$ kg, $m_p = 1.67 \times 10^{-27}$ kg, $c = 3 \times 10^8$ m/s, $1 \text{ eV} = 1.6 \times 10^{-19}$ J, $k_B = 1.38 \times 10^{-23}$ J K⁻¹ = 8.617×10^{-5} eV K⁻¹, $\mu_0 = 4\pi \times 10^{-7}$ H/m, Avogadro Number (N_A) = 6.023×10^{23} /mol, Bohr Magnetron (μ_B or β) = 9.27×10^{-24} A m², wherever required.

- Q 1.** A particle is trapped in an infinite one-dimensional potential well of width 'L'. Find the probability of finding the particle between $x=0$ and $x=L/2$ in its first excited state. **(10 M)**
- Q 2.** The high-purity Silicon is added with $1.5 \times 10^{23} \text{ m}^{-3}$ Boron atoms. (i) Is this material p-type or n-type? (ii) Calculate the electrical conductivity of this material at room temperature. Assume the mobility of the charge carriers is $0.042 \text{ m}^2/\text{V-s}$ at room temperature. **(10 M)**
- Q 3.** Find the intrinsic carrier concentration of Silicon at 27°C and 77°C whose band gap is 1.12 eV . Given that the effective mass of electron and hole are $0.28m_0$ and $0.15m_0$ respectively. **(10 M)**
- Q 4a.** A thermistor which is made of intrinsic silicon has a resistance of 450Ω at 300 K . Estimate its approximate resistance at 350 K , assuming a gap energy of silicon of 1.05 eV and that the carrier mobilities do not vary appreciably over this range of temperatures. **(5 M)**
- Q 4b.** The solar insolation on a rectangular module ($2.5 \text{ m} \times 3.5 \text{ m}$) of a photovoltaic cell is 950 W/m^2 . If the efficiency of the cells is 11.5% , find the power that can be generated with photovoltaic module? **(5 M)**
- Q 5.** Calculate the saturation magnetization and saturation flux density of Ni. Given the net magnetic moment per atom of 0.60 Bohr magnetons for Ni and a density of 8.90 g/cm^3 . Given the atomic mass of the Fe is 58.69 g/mol . **(10 M)**
- Q 6.** The B-H curve of an iron-silicon alloy is shown below and is kept within a coil of wire producing a magnetic field strength of having the B-H behaviour shown below is inserted within a coil of wire producing a magnetic field strength of 5 A/m . **(10 M)**

Phy?

Formula

$\mu_B = \frac{eh}{4\pi m_e}$

$\frac{2\pi m_e h^2}{4\pi}$

$X = 31846.133$

$R = e \frac{l}{A}$

$\frac{1}{e} = \frac{l}{AR}$